

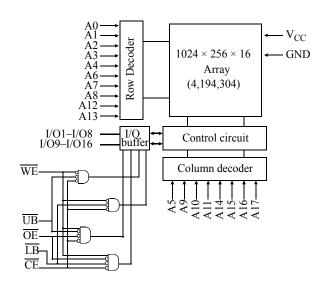
5.0 V 256 K × 16 CMOS SRAM

Features

- Pin compatible with AS7C4098
- Industrial and commercial temperature
- Organization: 262,144 words × 16 bits
- Center power and ground pins
- High speed
 - 10/12/15/20 ns address access time
 - 5/6 ns output enable access time
- Low power consumption: ACTIVE
 - 990mW/max @ 10 ns
- Low power consumption: STANDBY
- 55mW/max CMOS
- Individual byte read/write controls

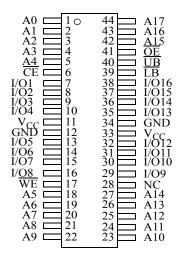
- Easy memory expansion with \overline{CE} , \overline{OE} inputs
- TTL- and CMOS-compatible, three-state I/O
- 44-pin JEDEC standard packages
 - 400-mil SOJ
 - TSOP 2
- ESD protection \geq 2000 volts
- Latch-up current $\geq 200 \text{ mA}$

Logic block diagram



Pin arrangement for SOJ and TSOP 2

44-pin (400 mil) SOJ TSOP2



Selection guide

	-10	-12	-15	-20	Unit
Maximum address access time	10	12	15	20	ns
Maximum output enable access time	5	6	6	6	ns
Maximum operating current	180	160	140	120	mA
Maximum CMOS standby current	10	10	10	10	mA



Functional description

The AS7C4098A is a high-performance CMOS 4,194,304-bit Static Random Access Memory (SRAM) device organized as 262,144 words × 16 bits. It is designed for memory applications where fast data access, low power, and simple interfacing are desired.

Equal address access and cycle times (t_{AA}, t_{RC}, t_{WC}) of 10/12/15/20 ns with output enable access times (t_{OE}) of 5/6 ns are ideal for high-performance applications. The chip enable input \overline{CE} permits easy memory expansion with multiple-bank memory systems.

When \overline{CE} is high the device enters standby mode. The device is guaranteed not to exceed 55mW power consumption in CMOS standby mode. A write cycle is accomplished by asserting write enable (\overline{WE}) and chip enable (\overline{CE}). Data on the input pins I/O1–I/O16 is written on the rising edge of \overline{WE} (write cycle 1) or \overline{CE} (write cycle 2). To avoid bus contention, external devices should drive I/O pins only after outputs have been disabled with output enable (\overline{OE}) or write enable (\overline{WE}).

A read cycle is accomplished by asserting output enable (\overline{OE}) and chip enable (\overline{CE}) , with write enable (\overline{WE}) high. The chip drives I/O pins with the data word referenced by the input address. When either chip enable or output enable is inactive, or write enable is active, output drivers stay in high-impedance mode.

The device provides multiple center power and ground pins, and separate byte enable controls, allowing individual bytes to be written and read. \overline{LB} controls the lower bits, I/O1–I/O8, and \overline{UB} controls the higher bits, I/O9–I/O16.

All chip inputs and outputs are TTL- and CMOS-compatible, and operation is for 5.0V (AS7C4098A) supply. The device is available in the JEDEC standard 400-mL, 44-pin SOJ, TSOP 2 packages.

Absolute maximum ratings

Parameter	Symbol	Min	Max	Unit
Voltage on V _{CC} relative to GND	V _{t1}	-0.50	+7.0	V
Voltage on any pin relative to GND	V _{t2}	-0.50	V _{CC} +0.50	V
Power dissipation	P_{D}	-	1.5	W
Storage temperature (plastic)	T_{stg}	-65	+150	°C
Ambient temperature with V _{CC} applied	T _{bias}	-55	+125	°C
DC current into outputs (low)	I _{OUT}	-	±20	mA

Note: Stresses greater than those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Truth table

CE	WE	OE	LB	UB	I/O1–I/O8	I/O9–I/O16	Mode
Н	X	X	X	X	High Z	High Z	Standby (I _{SB} , I _{SB1})
L	Н	Н	X	X	High 7	High 7	Output disable (I)
L	X	X	Н	Н	High Z	High Z	Output disable (I _{CC})
			L	Н	D _{OUT}	High Z	
L	Н	L	Н	L	High Z	D _{OUT}	Read (I _{CC})
			L	L	D _{OUT}	D _{OUT}	
			L	Н	D _{IN}	High Z	
L	L	X	Н	L	High Z	D _{IN}	
			L	L	D _{IN}	D_{IN}	Write (I _{CC})

Key: X = Don't care, L = Low, H = High.



Recommended operating conditions

Parameter	Symbol	Min	Typical	Max	Unit	
Supply voltage	V _{CC} (10/12/15/20)	4.5	5.0	5.5	V	
Input voltage	V _{IH} *	2.2	_	$V_{CC} + 0.5$	V	
input voltage	input voltage			_	0.8	V
Ambient operating temperature	commercial	$T_{\mathbf{A}}$	0	_	70	°C
Ambient operating temperature	industrial	$T_{\mathbf{A}}$	-40	_	85	°C

 $V_{IH} = V_{CC} + 1.5V$ for pulse width less than 5 nS.

DC operating characteristics (over the operating range)¹

			-1	10	-	12		15	-7	20		
Parameter	Symbol	Test conditions	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Input leakage current	$ I_{LI} $	$V_{CC} = Max$ $V_{IN} = GND \text{ to } V_{CC}$	_	1	-	1	-	1	_	1	μΑ	
Output leakage current	$ I_{LO} $	$V_{CC} = Max$ $\overline{CE} = V_{\underline{IH}} \text{ or } \overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$ $V_{I/O} = GND \text{ to } V_{CC}$	_	1	1	1	1	1	_	1	μΑ	
Operating power supply current	I _{CC}	$V_{CC} = Max$ $\overline{CE} \le V_{IL}, f = fmax, I_{OUT} = 0 mA$	-	180	-	160	-	140	-	120	mA	
Standby	I_{SB}	$\frac{V_{CC} = Max}{CE \ge V_{IH}, f = Max}$	-	60	1	55	ı	50	-	45	mA	
power supply current I _S	I_{SB1}	$\begin{aligned} \mathbf{V}_{CC} &= \mathbf{Max} \\ \overline{CE} &\geq \mathbf{V}_{CC} - 0.2 \mathbf{V}, \mathbf{V}_{IN} \geq \mathbf{V}_{CC} \\ &- 0.2 \mathbf{V} \text{ or } \mathbf{V}_{IN} \leq 0.2 \mathbf{V}, \mathbf{f} = 0 \end{aligned}$	-	10	-	10	-	10	-	10	mA	
Output	V _{OL}	$I_{OL} = 6 \text{ mA}, V_{CC} = \text{Min}$	_	0.4	_	0.4	_	0.4	_	0.4	V	4
Output voltage	OL	$I_{OL} = 8 \text{ mA}, V_{CC} = \text{Min}$	_	0.5	_	0.5	-	0.5	_	0.5	•	ſ
	V _{OH}	$I_{OH} = -4 \text{ mA}, V_{CC} = \text{Min}$	2.4	_	2.4	_	2.4	_	2.4	_	V	4

Capacitance (f = 1MHz, $T_a = 25^{\circ} C$, $V_{CC} = NOMINAL)^4$

Parameter	Symbol	Signals	Test conditions	Max	Unit
Input capacitance	C_{IN}	$A, \overline{CE}, \overline{WE}, \overline{OE}, \overline{UB}, \overline{LB}$	$V_{IN} = 0V$	6	pF
I/O capacitance	C _{I/O}	I/O	$V_{IN} = V_{OUT} = 0V$	8	pF

^{**} $V_{\rm IL}$ min = -1.0V for pulse width less than 5 nS.



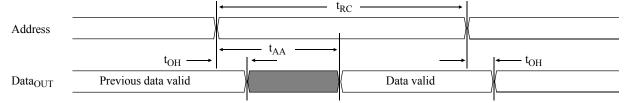
Read cycle (over the operating range)^{2,8}

		-10		-1	12	-1	15	-20			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Read cycle time	t_{RC}	10	_	12	_	15	_	20	_	ns	
Address access time	t_{AA}	-	10	_	12	_	15	_	20	ns	
Chip enable (CE) access time	t _{ACE}	_	10	_	12	_	15	_	20	ns	
Output enable (OE) access time	t_{OE}	-	5	_	6	_	6	_	6	ns	
Output hold from address change	t _{OH}	3	_	3	_	3	_	3	_	ns	4
CE Low to output in low Z	t_{CLZ}	3	_	3	_	3	_	3	_	ns	3, 4
CE High to output in high Z	t _{CHZ}	_	5	_	6	_	7	_	9	ns	3, 4
OE Low to output in low Z	t _{OLZ}	0	_	0	_	0	_	0	_	ns	3, 4
OE High to output in high Z	t _{OHZ}	_	5	_	6	_	7	_	9	ns	3, 4
LB, UB access time	t _{BA}	_	5	_	6	_	7	_	8	ns	
$\overline{\text{LB}}$, $\overline{\text{UB}}$ Low to output in low Z	$t_{ m BLZ}$	0	_	0	_	0	_	0	_	ns	
$\overline{\overline{LB}}$, $\overline{\overline{UB}}$ High to output in high Z t_{BH}		_	5	_	6	_	7	_	9	ns	
Power up time t _F		0	_	0	_	0	_	0	_	ns	4
Power down time	t _{PD}	_	10	_	12	-	15		20	ns	4

Key to switching waveforms

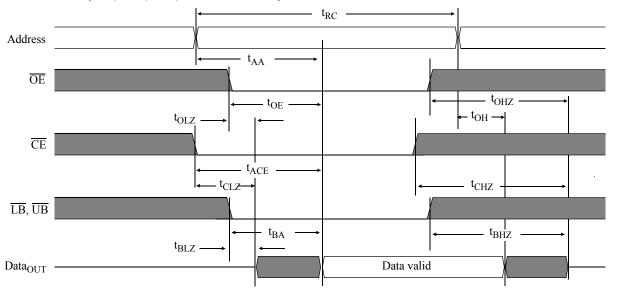
Rising input
Falling input
Undefined/don't care

Read waveform 1 (address controlled)^{5,6,8}





Read waveform 2 (CE, OE, UB, LB controlled)^{5,7,8}

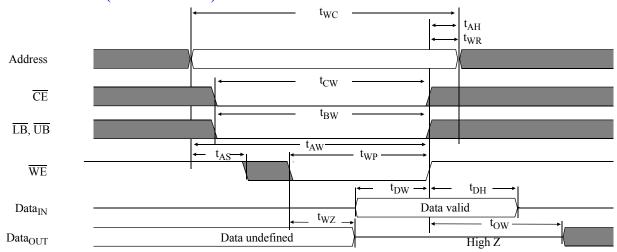


Write cycle (over the operating range)⁹

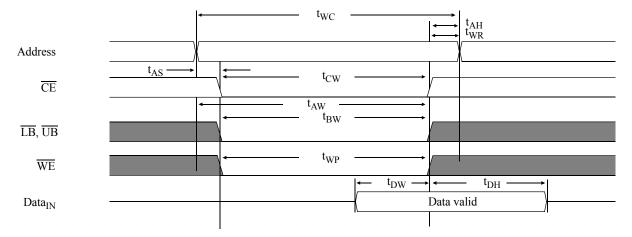
	-10		-12		_	-15		-20			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Note
Write cycle time	t_{WC}	10	_	12	_	15	_	20	_	ns	
Chip enable $\overline{\text{(CE)}}$ to write end	t_{CW}	7	_	8	_	10	-	12	-	ns	
Address setup to write end	t_{AW}	7	_	8	_	10	-	12	-	ns	
Address setup time	t _{AS}	0	_	0	_	0	-	0	-	ns	
Write pulse width (\overline{OE} = High)	t _{WP1}	7	_	8	_	10	_	12	_	ns	
Write pulse width $(\overline{OE} = Low)$	t _{WP2}	10	_	12	_	15	_	20	_	ns	
Write recovery time	t _{WR}	0	_	0	_	0	-	0	-	ns	
Address hold from end of write	t _{AH}	0	_	0	_	0	_	0	_	ns	
Data valid to write end	t_{DW}	5	_	6		7	-	9	-	ns	
Data hold time	t _{DH}	0	_	0	_	0	_	0	_	ns	3, 4
Write enable to output in High-Z	t_{WZ}	2	5	2	6	2	7	2	9	ns	3, 4
Output active from write end	t_{OW}	3	_	3	_	3	_	3	_	ns	3, 4
Byte enable Low to write end	t_{BW}	7	_	8	_	10	_	12	_	ns	3, 4



Write waveform 1(WE controlled)9

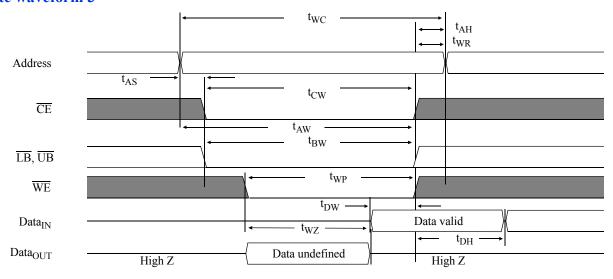


Write waveform 2 (CE controlled)9





Write waveform 3 9



AC test conditions

- Output load: see Figure B.
- Input pulse level: GND to $V_{\mbox{\footnotesize CC}}$ 0.5V. See Figure A.
- Input rise and fall times: 2 ns. See Figure A.
- Input and output timing reference levels: 1.5V.

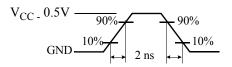


Figure A: Input pulse

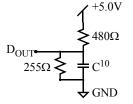
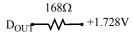


Figure B:5.0V Output load

Thevenin equivalent:

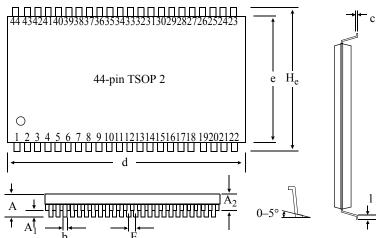


Notes

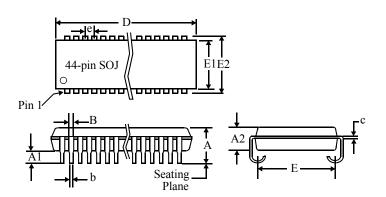
- 1 During V_{CC} power-up, a pull-up resistor to V_{CC} on \overline{CE} is required to meet I_{SB} specification.
- 2 For test conditions, see AC Test Conditions, Figures A and B.
- 3 t_{CLZ} and t_{CHZ} are specified with C_L = 5pF as in Figure B. Transition is measured ± 500 mV from steady-state voltage.
- 4 This parameter is guaranteed, but not tested.
- $\overline{\text{WE}}$ is High for read cycle.
- $\overline{\text{CE}}$ and $\overline{\text{OE}}$ are Low for read cycle.
- 7 Address valid prior to or coincident with \overline{CE} transition Low.
- 8 All read cycle timings are referenced from the last valid address to the first transitioning address.
- 9 All write cycle timings are referenced from the last valid address to the first transitioning address.
- 10 C = 30 pF, except on High Z and Low Z parameters, where C = 5 pF.



Package dimensions



	44-pin '	TSOP 2
	Min (mm)	Max (mm)
A		1.2
$\mathbf{A_1}$	0.05	0.15
A ₂	0.95	1.05
b	0.30	0.45
c	0.12	0.21
d	18.31	18.52
e	10.06	10.26
H _e	11.68	11.94
E	0.80 (t	ypical)
1	0.40	0.60



	44-pin SO	J 400 mils
	Min(mils)	Max(mils)
A	0.128	0.148
A1	0.025	-
A2	0.105	0.115
В	0.026	0.032
b	0.015	0.020
c	0.007	0.013
D	1.120	1.130
E	0.370	NOM
E 1	0.395	0.405
E2	0.435	0.445
e	0.050	NOM



Ordering Codes

Package	Version	10 ns	12 ns	15 ns	20 ns
SOJ	5.0V commercial	AS7C4098A-10JC	AS7C4098A-12JC	AS7C4098A-15JC	AS7C4098A-20JC
	5.0V industrial	AS7C4098A-10JI	AS7C4098A-12JI	AS7C4098A-15JI	AS7C4098A-20JI
TSOP 2	5.0V commercial	AS7C4098A-10TC	AS7C4098A-12TC	AS7C4098A-15TC	AS7C4098A-20TC
1501 2	5.0V industrial	AS7C4098A-10TI	AS7C4098A-12TI	AS7C4098A-15TI	AS7C4098A-20TI

Note: Add suffix 'N' to the above part numbers for Lead Free Parts. (Ex: AS7C4098A - 10TCN)

Part numbering system

AS7C	4098A	-XX	J or T	X	X
SRAM prefix	Device number	Access time	Packages: J: SOJ 400 mil T: TSOP 2	Temperature ranges: C: Commercial, 0°C to 70°C I: Industrial, –40°C to 85°C	N = Lead Free Parts



Revision History

Rev. No.	History	Revised Date
v1.0	Initial release	11/08/04
v1.1	Included I _{CC} , I _{SB} & I _{SB1} parameters	05/27/05
	Corrected the following: T _{OE} , V _{IH} , V _{OL} & t _{WZ}	
v1.2	Removed the title "PRELIMINARY INFORMATION"	02/21/06





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